

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

1. (currently amended): A resin encapsulating method for a semiconductor chip comprising adhering a silicone-based pressure-sensitive adhesive tape to a leadframe, bonding a semiconductor chip to the leadframe having the silicone-based pressure-sensitive adhesive tape adhered thereto, encapsulating the semiconductor chip with a resin in a mold, said resin being heated in the encapsulation step to a temperature of at least 180°C whereby the silicon-based pressure-sensitive adhesive tape is heated at least locally to a temperature of at least 180°C during the encapsulation step, and stripping the silicone-based pressure-sensitive adhesive tape,

wherein the silicone-based pressure-sensitive adhesive tape after being heated to a temperature of at least 180°C in the encapsulation step has a thermal shrinkage of 3% or less on resin encapsulating and a pressure-sensitive adhesive strength of 400gf/20 mm or less at 23°C after being heated to a temperature of at least 180°C in the encapsulation step followed by cooling after the silicone-based adhesive tape being heated at 180°C.

2. (currently amended): A resin encapsulating method for a semiconductor chip comprising adhering a silicone-based pressure-sensitive adhesive tape to a tape carrier film, bonding a semiconductor chip to the tape carrier film having the silicone-based pressure-sensitive adhesive tape adhered thereto, encapsulating the semiconductor chip with a resin in a mold, said resin being heated in the encapsulation step to a temperature of at least 180°C whereby the silicon-based pressure-sensitive adhesive tape is heated at least locally to a temperature of at least 180°C during the encapsulation step, and stripping the silicone-based pressure-sensitive adhesive tape,

wherein the silicone-based pressure-sensitive adhesive tape after being heated to a temperature of at least 180°C in the encapsulation step has a thermal shrinkage of 3% or less on resin encapsulating and a pressure-sensitive adhesive strength of 400gf/20 mm or less at 23°C

after being heated to a temperature of at least 180°C in the encapsulation step followed by cooling after the silicone-based adhesive tape being heated at 180°C.

Claims 3-5. (canceled).

6. (previously presented): The resin encapsulating method for a semiconductor chip according to Claim 1 or Claim 2, wherein the silicone-based pressure-sensitive adhesive tape has a thermal shrinkage of 2% or less on resin encapsulating.

7. (previously presented): The resin encapsulating method for a semiconductor chip according to Claim 1 or Claim 2, wherein the silicone-based pressure-sensitive adhesive tape has a thermal shrinkage of 1% or less on resin encapsulating.

8. (previously presented): The resin encapsulating method for a semiconductor chip according to Claim 1 or Claim 2, wherein the silicone-based pressure-sensitive adhesive tape has a pressure-sensitive adhesive strength of 300 gf/20 mm or less and 5 gf/20 mm or more.

9. (previously presented): The resin encapsulating method for a semiconductor chip according to Claim 1 or Claim 2, wherein the silicone-based pressure-sensitive adhesive tape further contains at least one heat-resistant filler.

10. (previously presented): The resin encapsulating method for a semiconductor chip according to Claim 1 or Claim 2, wherein the silicone-based pressure-sensitive adhesive tape comprises a substrate having a thickness from 5 to 250 µm.

11. (previously presented): The resin encapsulating method for a semiconductor chip according to Claim 1 or Claim 2, wherein the silicone-based pressure-sensitive adhesive tape comprises a substrate having a thickness from 5 to 100 µm.

12. (previously presented): The resin encapsulating method for a semiconductor chip according to Claim 1 or Claim 2, wherein the silicone-based pressure-sensitive adhesive tape comprises a pressure-sensitive adhesive layer having a thickness from 2 to 100 µm.

13. (previously presented): The resin encapsulating method for a semiconductor chip according to Claim 1 or Claim 2, wherein the silicone-based pressure-sensitive adhesive tape comprises a pressure-sensitive adhesive layer having a thickness from 5 to 75 µm.

14. (previously presented): The resin encapsulating method for a semiconductor chip according to Claim 1 or Claim 2, wherein the silicone-based pressure-sensitive adhesive tape comprises a pressure-sensitive adhesive layer containing a crosslinking agent.

15. (previously presented): The resin encapsulating method for a semiconductor chip according to Claim 1 or Claim 2, wherein the silicone-based pressure-sensitive adhesive tape comprises a substrate subjected to primer coating or surface roughening.

16. (previously presented): The resin encapsulating method for a semiconductor chip according to Claim 1 or Claim 2, wherein the silicone-based pressure-sensitive adhesive tape comprises a pressure-sensitive adhesive layer containing heat conductive particles.

17. (previously presented): The resin encapsulating method for a semiconductor chip according to Claim 1 or Claim 2, wherein the silicone-based pressure-sensitive adhesive tape comprises a pressure-sensitive adhesive layer containing conductive particles.

18. (previously presented): The resin encapsulating method for a semiconductor chip according to Claim 1 or Claim 2, wherein the silicone-based pressure-sensitive adhesive tape comprises a pressure-sensitive adhesive layer used in a TAB system.

19. (previously presented): The resin encapsulating method for a semiconductor chip according to Claim 1 or Claim 2, wherein the silicone-based pressure-sensitive adhesive tape has an initial pressure-sensitive adhesive strength of about 220 gf/20 mm or less.